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ATTY DOCKET NO.

SERIAL NO.

211147US99

09/903,784

## LIST OF REFERENCES CITED BY APPLICANT

APPLICANT  
AROON TUNGARE ET ALFILING DATE  
JULY 13, 2001GROUP  
2826

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
FE	AA	3,802,967	04/09/74	Ladany et al.			
	AB	4,174,422	11/13/79	Matthews et al.			
	AC	4,404,265	09/13/83	Manasevit			
	AD	4,482,906	11/13/84	Hovel et al.			
	AE	4,523,211	06/11/85	Morimoto et al.			
	AF	4,661,176	04/28/87	Manasevit			
	AG	4,793,872	12/27/88	Meunier et al.			
	AH	4,846,926	07/11/89	Kay et al.			
	AJ	4,855,249	08/08/89	Akasaki et al.			
	AI	4,891,091	01/02/90	Shastri			
	AK	4,912,087	03/27/90	Aslam et al.			
	AL	4,928,154	05/22/90	Umeno et al.			
	AM	4,963,949	10/16/90	Wanlass et al.			
	AN	5,141,894	08/25/92	Bisaro et al.			
	AO	5,159,413	10/27/92	Calviello et al.			
	AP	5,173,474	12/22/92	Connell et al.			
	AQ	5,221,367	06/22/93	Chisholm et al.			
	AR	5,225,031	07/06/93	McKee et al.			
	AS	5,358,925	10/25/94	Neville Connell et al.			
	AT	5,393,352	02/28/95	Summerfelt			
	AU	5,418,216	05/23/95	Fork			
	AV	5,450,812	09/19/95	McKee et al.			
	AW	5,478,653	12/26/95	Guenzer			
	AX	5,482,003	01/09/96	McKee et al.			
	AY	5,514,484	05/07/96	Nashimoto			
	AZ	5,556,463	09/17/96	Guenzer			
	BA	5,588,995	12/31/96	Sheldon			
	BB	5,670,798	09/23/97	Schetzina			
	BC	5,733,641	03/31/98	Fork et al.			
	BD	5,735,949	04/07/98	Mantl et al.			
	BE	5,741,724	04/21/98	Ramdani et al.			
	BF	5,810,923	09/22/98	Yano et al.			
	BG	5,830,270	11/03/98	McKee et al.			
	BH	5,912,068	06/15/99	Jia			
	BI	6,020,222	02/01/00	Wollesen			
	BJ	6,045,626	04/04/00	Yano et al.			
	BK	6,064,078	05/16/00	Northrup et al.			
	BL	6,064,092	05/16/00	Park			
	BM	6,096,584	08/01/00	Ellis-Monaghan et al.			
	BN	6,103,008	08/15/00	McKee et al.			
	BO	6,136,666	10/24/00	So			
	BP	6,174,755	01/16/01	Manning			
	BQ	6,180,486	01/30/01	Leobandung et al.			

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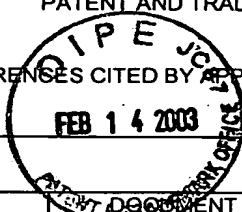
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JULY 13, 2001GROUP  
2826

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EXAMINER INITIAL		PATENT DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
PC	CA	3,766,370	10/16/73	Walther			
	CB	4,006,989	02/08/77	Andringa			
	CC	4,284,329	08/18/81	Smith et al.			
	CD	4,777,613	10/11/98	Shahan et al.			
	CE	4,802,182	01/31/89	Thornton et al.			
	CF	4,882,300	11/21/89	Inoue et al.			
	CG	4,896,194	01/23/90	Suzuki			
	CH	4,999,842	03/12/91	Huang et al.			
	CI	5,081,062	01/14/92	Vasudev et al.			
	CJ	5,155,658	10/13/92	Inam et al.			
	CK	5,248,564	09/28/93	Ramesh			
	CL	5,260,394	11/09/93	Tazaki et al.			
	CM	5,270,298	12/14/93	Ramesh			
	CN	5,286,985	02/15/94	Taddiken			
	CO	5,310,707	05/10/94	Oishi et al.			
	CP	5,326,721	07/05/94	Summerfelt			
	CQ	5,404,581	04/04/95	Honjo			
	CR	5,418,389	05/23/95	Watanabe			
	CS	5,436,759	07/25/95	Dijail et al.			
	CT	5,576,879	11/19/96	Nashimoto			
	CU	5,606,184	02/25/97	Abrokwah, et al.			
	CV	5,640,267	06/17/97	May et al.			
	CW	5,674,366	10/07/97	Hayashi et al.			
	CX	5,729,641	03/17/98	Chandonnet et al.			
	CY	5,790,583	08/04/98	Ho			
	CZ	5,825,799	10/20/98	Ho et al.			
	DA	5,857,049	01/05/99	Beranek et al.			
	DB	5,874,860	02/23/99	Brunel et al.			
	DC	5,926,496	07/20/99	Ho et al.			
	DD	5,937,285	08/10/99	Abrokwah, et al.			
	DE	5,981,400	11/09/99	Lo			
	DF	5,990,495	11/23/99	Ohba			
	DG	6,002,375	12/14/99	Corman et al.			
	DH	6,008,762	12/28/99	Nghiem			
	DI	6,055,179	04/25/00	Koganei et al.			
	DJ	6,107,653	08/22/00	Fitzgerald			
	DK	6,113,690	09/05/00	Yu et al.			
	DL	6,114,996	09/05/00	Nghiem			
	DM	6,121,642	09/19/00	Newns			
	DN	6,128,178	10/03/00	Newns			
	DO	6,143,072	11/07/00	McKee et al.			
	DP	6,184,144	02/06/01	Lo			
	DQ	6,222,654	04/24/01	Frigo			

Form PTO 1449  
(Modified)U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

SERIAL NO.

211147US99

09/903,784

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APPLICANT  
AROON TUNGARE ET ALFILING DATE  
JULY 13, 2001GROUP  
2826

FEB 14 2003

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EXAMINER	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	EA	4,484,332	11/20/84	Hawrylo		
	EB	4,815,084	03/21/89	Scifres et al.		
	EC	4,876,219	10/24/89	Eshita et al.		
	ED	4,963,508	10/16/90	Umeno et al.		
	EE	5,060,031	10/22/91	Abrokwah, et al.		
	EF	5,063,166	11/05/91	Mooney et al.		
	EG	5,116,461	05/26/92	Lebby et al.		
	EH	5,127,067	06/30/92	Delcoco et al.		
	EI	5,144,409	09/01/92	Ma		
	EJ	5,293,050	03/08/94	Chapple-Sokol et al		
	EK	5,356,831	10/18/94	Calviello et al.		
	EL	5,391,515	02/21/95	Kao et al.		
	EM	5,442,191	08/15/95	Ma		
	EN	5,444,016	08/22/95	Abrokwah, et al.		
	EO	5,480,829	01/02/96	Abrokwah, et al.		
	EP	5,528,414	06/18/96	Oakley		
	EQ	5,614,739	03/25/97	Abrokwah et al.		
	ER	5,729,394	03/17/98	Sevier et al.		
	ES	5,731,220	03/24/98	Tsu et al.		
	ET	5,764,676	06/09/98	Paoli et al.		
	EU	5,777,762	07/07/98	Yamamoto		
	EV	5,778,018	07/07/98	Yoshikawa et al.		
	EW	5,778,116	07/07/98	Tomich		
	EX	5,801,105	09/01/98	Yano et al.		
	EY	5,828,080	10/27/98	Yano et al.		
	EZ	5,858,814	01/12/99	Goossen et al.		
	FA	5,861,966	01/19/99	Ortel		
	FB	5,883,996	03/16/99	Knapp et al.		
	FC	5,995,359	11/30/99	Klee et al.		
	FD	6,058,131	05/02/00	Pan		
	FE	6,137,603	10/24/00	Henmi		
	FF	6,146,906	11/14/00	Inoue et al.		
	FG	6,173,474	01/16/01	Conrad		
	FH	6,180,252	01/30/01	Farrell et al.		
	FI	4,242,595	12/30/0	Lehovec		
	FJ	4,398,342	08/16/83	Pitt et al.		
	FK	4,424,589	01/03/84	Thomas et al.		
	FL	4,876,208	10/24/89	Gustafson et al.		
	FM	4,482,422	11/84	McGinn et al.		
	FN	4,667,088	05/19/87	Kramer		
	FO	4,772,929	09/20/88	Manchester et al.		
	FP	4,841,775	06/27/89	Ikeda et al.		
	FQ	4,845,044	07/04/89	Ariyoshi et al.		

Form PTO 1449  
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PATENT AND TRADEMARK OFFICE

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211147US99

09/903,784

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APPLICANT  
AROON TUNGARE ET ALFILING DATE  
JULY 13, 2001GROUP  
2826

FEB 14 2003

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GA	4,868,376	09/19/89	Lessin et al.			
GB	4,885,376	12/05/89	Verkade			
GC	4,888,202	12/89	Murakami et al.			
GD	4,891,091	12/90	Wanlass et al.			
GE	5,051,790	09/24/91	Hammer			
GF	5,055,445	10/08/91	Belt et al.			
GG	5,081,519	11/14/92	Nishimura et al.			
GH	5,143,854	09/01/92	Pirung et al.			
GI	5,185,589	02/09/93	Krishnaswamy et al.			
GJ	5,191,625	03/02/93	Gustavsson			
GK	5,194,397	03/16/93	Cook et al.			
GL	5,208,182	05/04/93	Narayan et al.			
GM	5,216,729	06/01/93	Berger et al.			
GN	5,314,547	05/24/94	Heremans et al.			
GO	5,352,926	10/04/94	Andrews			
GP	5,356,509	10/18/94	Terranova et al.			
GQ	5,371,734	12/06/94	Fischer			
GR	5,372,992	12/94	Itozaki et al.			
GS	5,405,802	04/11/95	Yamagata et al.			
GT	5,442,561	08/15/95	Yoshizawa et al.			
GU	5,453,727	09/26/95	Shibasaki et al.			
GV	5,466,631	11/14/95	Ichikawa et al.			
GW	5,473,047	12/05/95	Shi			
GX	5,473,171	12/95	Summerfelt			
GY	5,479,033	12/26/95	Baca et al.			
GZ	5,486,406	01/23/96	Shi			
HA	5,491,461	02/13/96	Partin et al.			
HB	5,492,859	02/20/96	Sakaguchi et al.			
HC	5,494,711	02/27/96	Takeda et al.			
HD	5,504,035	04/02/96	Rostoker et al.			
HE	5,504,183	04/02/96	Shi			
HF	5,511,238	04/23/96	Bayraktaroglu			
HG	5,512,773	04/96	Wolf et al.			
HH	5,515,047	05/07/96	Yamakido et al.			
HI	5,515,810	05/14/96	Yamashita et al.			
HJ	5,519,235	05/96	Ramesh			
HK	5,549,977	08/96	Jin et al.			
HL	5,551,238	09/03/96	Prueitt			
HM	5,552,547	09/03/96	Shi			
HN	5,589,284	12/31/96	Summerfelt et al.			
HO	5,602,418	02/11/97	Imai et al.			
HP	5,633,724	05/27/97	King et al.			

Form PTO 1449  
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PATENT AND TRADEMARK OFFICE

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APPLICANT  
AROON TUNGARE ET ALFILING DATE  
JULY 13, 2001GROUP  
2826

FEB 14 2003

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
IA		5,650,646	07/22/97	Summerfelt			
IB		5,656,382	08/12/97	Nashimoto			
IC		5,659,180	08/19/97	Shen et al.			
ID		5,661,112	08/26/97	Hatta et al.			
IE		5,679,965	11/95	Schetzina			
IF		5,725,641	03/10/98	MacLeod			
IG		5,745,631	04/28/98	Reinker			
IH		5,776,621	07/07/98	Nashimoto			
II		5,777,350	07/07/98	Nakamura et al.			
IJ		5,789,845	08/04/98	Wadaka et al.			
IK		5,792,569	08/11/98	Sun et al.			
IL		5,792,679	08/11/98	Nakato			
IM		5,796,648	08/18/98	Kawakubo et al.			
IN		5,801,072	09/01/98	Barber			
IO		5,812,272	09/22/98	King et al.			
IP		5,814,583	09/98	Itozaki et al.			
IQ		5,825,055	10/20/98	Summerfelt			
IR		5,827,755	10/27/98	Yonchara et al.			
IS		5,833,603	11/10/98	Kovacs et al.			
IT		5,838,035	11/17/98	Ramesh			
IU		5,844,260	12/01/98	Ohori			
IV		5,846,846	12/08/98	Suh et al.			
IW		5,863,326	01/26/99	Nause et al.			
IX		5,872,493	02/16/99	Ella			
IY		5,879,956	03/99	Seon et al.			
IZ		5,880,452	03/09/99	Plesko			
JA		5,883,564	03/16/99	Partin			
JB		5,907,792	05/25/99	Droopad et al.			
JC		5,937,274	08/10/99	Kondow et al.			
JD		5,948,161	09/07/99	Kizuki			
JE		5,959,879	09/28/99	Koo			
JF		5,966,323	10/99	Chen et al.			
JG		5,987,011	11/16/99	Toh			
JH		6,022,140	02/08/00	Fraden et al.			
JI		6,022,410	02/08/00	Yu et al.			
JJ		6,023,082	02/08/00	McKee et al.			
JK		6,028,853	02/22/00	Haartsen			
JL		6,049,702	04/11/00	Tham et al.			
JM		6,078,717	06/20/00	Nashimoto et al			
JN		6,088,216	07/00	Laibowitz et al.			
JO		6,090,659	07/00	Laibowitz et al.			
JP		6,107,721	08/22/00	Lakin			
JQ		6,153,010	11/28/00	Kiyoku et al			

Form PTO 1449 U.S. DEPARTMENT OF COMMERCE  
(Modified) PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

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JULY 13, 2001GROUP  
2826

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
KA	6,153,454	11/28/00	Krivokapic			
KB	6,191,011	02/01	Gilboa et al			
KC	6,204,737	03/20/01	Ella			
KD	6,224,669	05/01/01	Yi et al.			
KE	6,225,051	05/01/01	Sugiyama et al.			
KF	6,241,821	06/05/01	Yu et al.			
KG	6,265,749	07/24/01	Gardner et al.			
KH	6,313,486	11/01	Kencke et al.			
KI	6,316,832	11/13/01	Tsuzuki et al.			
KJ	2002/0008234	01/02	Emrick			
KK	3,670,213	06/13/72	Nakawaga et al.			
KL	4,756,007	07/05/88	Qureshi et al.			
KM	4,773,063	09/20/88	Hunsperger et al.			
KN	5,394,489	02/28/95	Koch			
KO	5,406,202	04/11/95	Mehrgardt et al.			
KP	5,528,067	06/18/96	Farb et al.			
KQ	5,572,052	11/05/96	Kashihara et al.			
KR	5,767,543	06/16/98	Ooms et al.			
KS	6,175,497	01/16/01	Tseng et al.			
KT	6,197,503	03/06/01	Vo-Dinh et al.			
KU	6,248,459	06/19/01	Wang et al.			
KV	6,252,261	06/26/01	Usui et al.			
KW	6,255,198	07/03/01	Linthicum et al.			
KX	6,268,269	07/31/01	Lee et al.			
KY	6,291,319	09/18/01	Yu et al.			
KZ	6,316,785	11/13/01	Nunoue et al.			
LA	6,343,171	01/29/02	Yoshimura et al.			
LB	4,965,649	10/23/90	Zanio et al.			
LC	6,253,649	05/01	Kawahara et al.			
LD	6,211,096	04/01	Allman et al.			
LE	6,239,449	05/29/01	Fafard et al.			
LF	2001/0013313	08/16/01	Droopad et al.			
LG	6,184,044	02/06/01	Sone et al.			
LH	6,011,646	01/04/00	Mirkarimi et al.			
LI	5,227,196	07/13/93	Itoh			
LJ	6,150,239	11/21/00	Goesele et al.			
LK	5,441,577	08/15/95	Sasaki et al.			
LL	4,459,325	07/10/84	Nozawa et al.			
LM	4,392,297	07/12/83	Little			
LN	4,289,920	09/15/81	Hovel			
LO	5,281,834	01/25/94	Cambou et al.			
LP	4,901,133	02/13/90	Curran et al.			
LQ	5,514,904	05/07/96	Onga et al.			

Form PTO 1449  
(Modified)U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

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SERIAL NO.

09/903,784

APPLICANT

AROON TUNGARE ET AL

FILING DATE

JULY 13, 2001

GROUP

2826

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FE	MA	5,553,089	09/03/96	Seki et al.			
	MB	5,528,057	06/18/96	Yanagase et al.			
	MC	6,229,159	05/08/01	Suzuki			
	MD	4,748,485	05/31/88	Vasudev			
	ME	4,984,043	01/08/91	Vinal			
	MF	5,754,319	05/19/98	Van De Voorde et al.			
	MG	6,108,125	08/22/00	Yano			
	MH	5,073,981	12/17/91	Giles et al.			
	MI	5,140,651	08/18/92	Soref et al.			
	MJ	5,610,744	03/11/97	Ho et al.			
	MK	6,362,017	03/26/02	Manabe et al.			
	ML	6,242,686	06/05/01	Kishimoto et al.			
	MM	5,689,123	11/18/97	Major et al.			
	MN	5,670,800	09/23/97	Nakao et al.			
	MO	5,067,809	11/26/91	Tsubota			
	MP	5,596,205	01/21/97	Reedy et al.			
	MQ	6,175,555	01/16/01	Hoole			
	MR	5,357,122	10/18/94	Okubora et al.			
	MS	4,084,130	04/11/78	Holton			
	MT	6,093,302	07/25/00	Montgomery			
	MU	6,372,813	04/16/02	Johnson et al.			
	MV	5,608,046	03/04/97	Cook et al.			
	MW	5,955,591	09/21/99	Imbach et al.			
	MX	6,022,963	02/08/00	McGall et al.			
	MY	6,083,697	07/04/00	Beecher et al.			
	MZ	5,063,081	11/05/91	Cozzette et al.			
	NA	5,479,317	12/26/95	Ramesh			
	NB	5,306,649	04/26/94	Hebert			
	NC	5,962,069	10/05/99	Schindler et al.			
	ND	5,541,422	07/30/96	Wolf et al.			
	NE	5,873,977	02/23/99	Desu et al.			
	NF	5,538,941	07/23/96	Findikoglu et al.			
	NG	6,046,464	04/04/00	Schetzina			
	NH	6,235,145	05/22/01	Li et al.			
	NI	5,610,744	03/11/97	Ho et al.			
	NJ	5,280,013	01/18/94	Newman et al.			
	NK	6,348,373 B1	02/19/02	Ma et al.			
	NL	6,339,664 B1	01/15/02	Farjady et al.			
	NM	4,439,014	03/27/84	Stacy et al.			
	NN	4,889,402	12/26/89	Reinhart			
	NO	5,963,291	10/05/99	Wu et al.			
	NP	6,011,641	01/04/00	Shin et al.			
	NQ	6,340,788 B1	01/22/02	King et al.			

Form PTO 1449  
(Modified)U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

211147US99

SERIAL NO.

09/903,784

APPLICANT

AROON TUNGARE ET AL

FILING DATE

JULY 13, 2001

GROUP

2826

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
RE	OA	5,807,440	09/15/98	Kubota et al.			
	OB	4,681,982	07/21/87	Yoshida			
	OC	4,629,821	12/16/86	Bronstein-Bonte et al.			
	OD	4,452,720	06/05/84	Harada et al.			
	OE	3,935,031	01/27/76	Adler			
	OF	5,760,426	06/02/98	Marx et al.			
	OG	5,053,835	10/01/91	Horikawa et al.			
	OH	6,326,645 B1	12/04/01	Kadota			
	OI	5,770,887	06/23/98	Tadatomo et al.			
	OJ	6,372,356 B1	04/16/02	Thornton et al.			
	OK	4,774,205	09/27/88	Choi et al.			
	OL	6,359,330 B1	03/19/02	Goudard			
	OM	5,312,765	05/17/94	Kanber			
	ON	5,734,672	03/31/98	McMinn et al.			
	OO	6,367,699 B2	04/09/02	Ackley			
	OP	5,530,235	06/25/96	Stefik et al.			
	OQ	5,623,552	04/22/97	Lane			
	OR	5,481,102	01/02/96	Hazellrigg, Jr.			
	OS	6,134,114	10/17/00	Ungermann et al.			
	OT	5,984,190	11/16/99	Nevill			
	OU	5,789,733	08/04/98	Jachimowicz et al.			
	OV	5,753,300	05/19/98	Wessels et al.			
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	PF	6,392,257	05/21/02	Ramdani et al.			
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	PJ	5,132,648	07/21/92	Trinh et al.			
	PK	6,427,066	07/30/02	Grub			
	PL	2002/0072245	06/13/02	Ooms et al.			
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	PN	5,888,296	03/30/99	Ooms et al.			
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09/903,784

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AROON TUNGARE ET AL

FILING DATE

JULY 13, 2001

GROUP

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	QC	5,834,362	11/10/98	Miyagaki et al.			
	QD	6,248,621 B1	06/19/01	Wilk et al.			
	QE	5,266,355	11/30/93	Wernberg et al.			
	QF	6,277,436 B1	08/21/01	Stauf et al.			
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	QH	5,619,051	04/08/97	Endo			
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	QJ	5,210,763	05/11/93	Lewis et al.			
	QK	5,103,494	04/07/92	Mozer			
	QL	4,594,000	06/10/86	Falk et al.			
	QM	4,297,656	10/27/81	Pan			
	QN	5,244,818	09/14/93	Jokers et al.			
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	QV	4,910,164	03/20/90	Shichijo			
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	QX	6,121,647	09/19/00	Yano et al.			
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	RM	5,621,227	04/15/97	Joshi			
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	RO	5,163,118	11/10/92	Lorenzo et al.			
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211147US99

SERIAL NO.

09/903,784

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	SD	5,452,118	09/19/95	Maruska			
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	SF	6,300,615 B1	10/09/01	Shinohara et al.			
	SG	6,232,910 B1	05/15/01	Bell et al.			
	SH	5,686,741	11/11/97	Ogori et al.			
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	SK	6,410,947 B1	06/25/02	Wada			
	SL	6,417,059 B2	07/09/02	Huang			
	SM	6,461,927 B1	10/08/02	Mochizuki et al.			
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	TM	5,173,835	12/22/92	Cornett et al.			
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	TO	6,139,483	10/31/00	Seabaugh et al.			
	TP	5,283,462	02/01/94	Stengel			
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SERIAL NO.

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AROON TUNGARE ET AL

FILING DATE

JULY 13, 2001

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	UB	5,427,988	06/27/95	Sengupta et al.			
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	UD	5,682,046	10/28/97	Takahashi et al.			
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ATTY DOCKET NO.

SERIAL NO.

211147US99

09/903,784

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AROON TUNGARE ET AL

FILING DATE

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GROUP

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	AAA	0 250 171	12/23/87	EP	X	
	AAB	0 342 937	11/23/89	EP	X	
	AAC	0 455 526	06/11/91	EP	X	
	AAD	0 602 568	06/22/94	EP	X	
	AAE	0 607 435	07/27/94	EP	X	
	AAF	1 001 468	05/17/00	EP	X	
	AAG	0 514 018	11/19/92	EP	X	
	AAH	0 999 600	05/10/00	EP	X	
	AAI	1 319 311	06/04/70	Great Britain	X	
	AAJ	5-291299	11/05/93	Japan w/English Abstract	X	
	AAK	11-238683	08/31/99	Japan	X	
	AAL	11-260835	09/24/99	Japan w/English Abstract	X	
	AAM	HEI 2-391	01/05/90	Japan w/English Abstract	X	
	AAN	5-48072	02/26/93	Japan w/English Abstract	X	
	AAO	52-88354	07/23/77	Japan w/English Abstract	X	
	AAP	54-134554	10/19/79	Japan w/English Abstract	X	
	AAQ	55-87424	07/02/80	Japan w/English Abstract	X	
	AAR	61-108187	05/26/86	Japan w/English Abstract	X	
	AAS	6-232126	08/19/94	Japan	X	
	AAT	6-291299	10/18/94	Japan w/English Abstract	X	
	AAU	63-34994	02/15/88	Japan w/English Abstract	X	
	AAV	63-131104	06/03/88	Japan w/English Abstract	X	
	AAW	63-198365	08/17/88	Japan w/English Abstract	X	
	AAX	10-321943	12/04/98	Japan	X	
	AAY	6-334168	12/02/94	Japan	X	
	AAZ	WO 99/63580	12/09/99	WIPO	X	
	ABA	WO 99/14804	03/25/99	WIPO	X	
	ABB	WO 97/45827	12/04/97	WIPO		
	ABC	WO 99/19546	04/22/99	WIPO		
	ABD	WO 00/33363	06/08/00	WIPO		
	ABE	WO 00/48239	08/17/00	WIPO		
	ABF	WO 99/14797	03/25/99	WIPO		
	ABG	GB 2 335 792	09/29/99	Great Britain		
	ABH	1 109 212	06/20/01	Europe		
	ABI	DE 197 12 496	10/30/97	Germany		X
	ABJ	60-212018	10/24/85	Japan w/English Abstract		
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	ABL	WO 92/10875	06/25/92	WIPO		
	ABM	0 682 266	11/15/95	Europe		
	ABN	3-41783	02/91	Japan (English Abstract only)		
	ABO	0 581 239	02/02/94	Europe		
	ABP	0812494	01/16/96	Japan		
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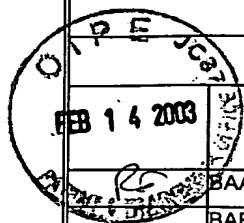
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	BAB	2000-068466	03/00	Japan (Abstract)		
	BAC	64-50575	02/27/89	Japan		
	BAD	WO 98/05807	01/12/98	WIPO		
	BAE	WO 94/03908	02/17/94	WIPO		
	BAF	WO 01/33585	05/10/01	WIPO		
	BAG	1-102435	04/20/89	Japan w/English Abstract		
	BAH	52-135684	11/12/77	Japan (English Abstract)		
	BAI	02051220	02/21/90	Japan (English Abstract)		
	BAJ	11135614	05/21/99	Japan (w/English Abstract)		
	BAK	64-52329	02/28/89	Japan (w/English Abstract)		
	BAL	10-256154	09/25/98	Japan (w/English Abstract)		
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	BAN	10-303396	11/13/98	Japan (w/English Abstract)		
	BAO	58-213412	12/12/83	Japan w/English Abstract		
	BAP	0 964 259	12/15/99	Europe		
	BAQ	0 875 922	11/04/98	Europe		
	BAR	61-63015	04/01/86	Japan w/English Abstract		
	BAS	11340542	12/10/99	Japan (English Abstract)		
	BAT	WO 01/37330	05/25/01	WIPO		
	BAU	0 331 467	09/06/89	Europe		
	BAV	WO 00/16378	03/23/00	WIPO		
	BAW	0 926 739	06/30/99	Europe		
	BAX	0 964 453	12/15/99	Europe		
	BAY	5-152529	06/18/93	Japan w/English Abstract		
	BAZ	9-67193	03/11/97	Japan w/English Abstract		
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	BBB	0 309 270	03/29/89	Europe		
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	BBF	DE 100 17 137	10/26/00	GERMANY		
	BBG	WO 02 01648	01/03/02	WIPO		
	BBH	WO 02/33385 A2	04/25/02	WIPO		
	BBI	WO 01/59814 A2	08/16/01	WIPO		
	BBJ	WO 02/09160 A2	01/31/02	WIPO		
	BBK	WO 00/06812	02/10/00	WIPO		
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	BBM	0 538 611	04/28/93	Europe		
	BBN	WO 01/59820 A1	08/16/01	WIPO		
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Form PTO 1449  
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PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

SERIAL NO.

211147US99

09/903,784

APPLICANT  
AROON TUNGARE ET ALFILING DATE  
JULY 13, 2001GROUP  
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	CAB	EP 1 069 606	01/17/01	Europe		
	CAC	WO 02/03113	01/10/02	WIPO		
	CAD	WO 02/03467	01/10/02	WIPO		
	CAE	0 630 057	12/21/94	EUROPE		
	CAF	61-36981	02/21/86	Japan w/English Abstract		
	CAG	WO 93/07647	04/15/93	WIPO		
	CAH	2002-9366	01/11/02	Japan w/English Abstract		
	CAI	EP 0 881 669	12/02/98	Europe		
	CAJ	WO 02/03480	01/10/02	WIPO		
	CAK	WO 02/50879	06/27/02	WIPO		
	CAL	EP 0 777 379	06/04/97	Europe		
	CAM	WO 01/04943 A1	01/18/01	WIPO		xx
	CAN	WO 02/47127 A2	06/13/02	WIPO		
	CAO	JP 58-075868	05/07/83	Japan w/English Abstract		
	CAP	EP 0 993 027	04/12/00	Europe		
	CAQ	EP 0 711 853	05/15/96	Europe		
	CAR	WO 98/20606	05/14/98	WIPO		
	CAS	EP 1 043 765	10/11/00	Europe		
	CAT	0 300 499	01/25/89	Europe		
	CAU	EP 1 085 319	03/21/01	Europe		
	CAV	WO 01/16395	03/08/01	WIPO		
	CAW	2000-351692	12/19/00	Japan w/English Abstract		
	CAX	03-188619	08/16/91	Japan (English Abstract only)		
	CAY	63-289812	11/28/88	Japan (English Abstract only)		
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	CBA	06-069490	03/11/94	Japan (English Abstract only)		
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	CCAD	Wang et al., "Processing and Performance of Piezoelectric Films", Univ. Of MD, Wilcoxon Research Col, and Motorola Labs, May 11, 2000.	
	CCAE	M. Rotter et al., "Nonlinear Acoustoelectric Interactions in GaAs/LiNbO <sub>3</sub> Structures", <i>Applied Physics Letters</i> , Vol. 75(7), August 16, 1999, pp. 965-967.	
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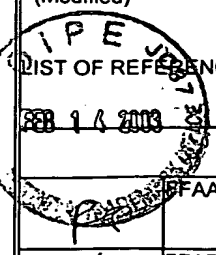
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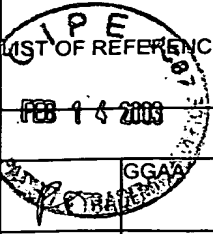


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